

NCE N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The NCE0128D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

GENERAL FEATURES

- $V_{DS} = 100V, I_D = 28A$
 $R_{DS(ON)} < 26m\Omega @ V_{GS}=10V$ (Typ: 13.3 m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

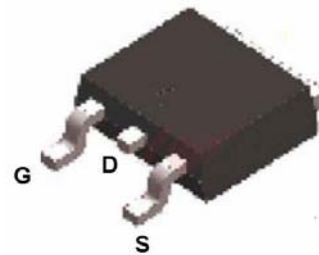
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



Schematic diagram



Marking and pin Assignment



TO-263-2L top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0128D	NCE0128D	TO-263-2L	-	-	-

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	28	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	20	A
Pulsed Drain Current	I_{DM}	190	A
Maximum Power Dissipation	P_D	63	W
Derating factor		0.42	W/°C
Single pulse avalanche energy (Note 5)	E_{AS}	550	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	2.4	$^{\circ}\text{C/W}$
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Electrical Characteristics (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=16A$		13.3	26	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=16A$	30			S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$		3700		PF
Output Capacitance	C_{oss}			630		PF
Reverse Transfer Capacitance	C_{rss}			330		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=16A$ $V_{GS}=10V, R_{GEN}=2.5\Omega$		12		nS
Turn-on Rise Time	t_r			55		nS
Turn-Off Delay Time	$t_{d(off)}$			45		nS
Turn-Off Fall Time	t_f			47		nS
Total Gate Charge	Q_g	$V_{DS}=80V, I_D=16A,$ $V_{GS}=10V$		95		nC
Gate-Source Charge	Q_{gs}			18		nC
Gate-Drain Charge	Q_{gd}			25		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=16A$		0.85	1.2	V
Diode Forward Current (Note 2)	I_S				57	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = 16A$ $di/dt = 100A/\mu s(\text{Note}3)$		140	220	nS
Reverse Recovery Charge	Q_{rr}			650	1000	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test circuit

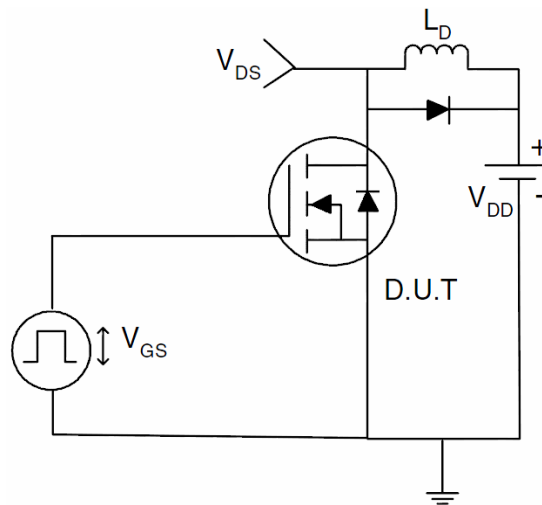
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

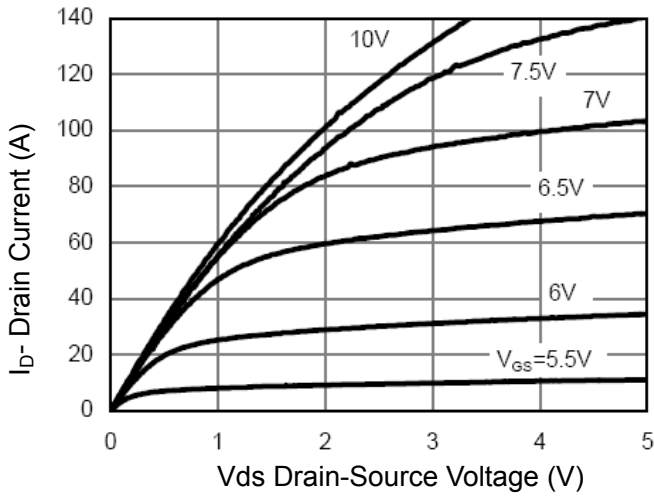


Figure 1 Output Characteristics

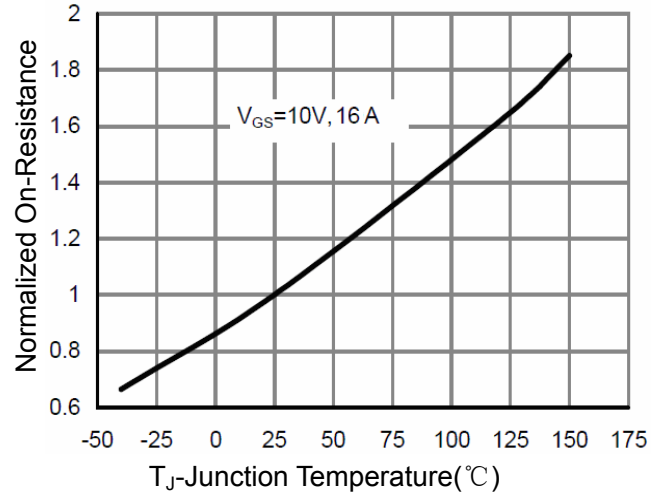


Figure 4 Rdson-Junction Temperature

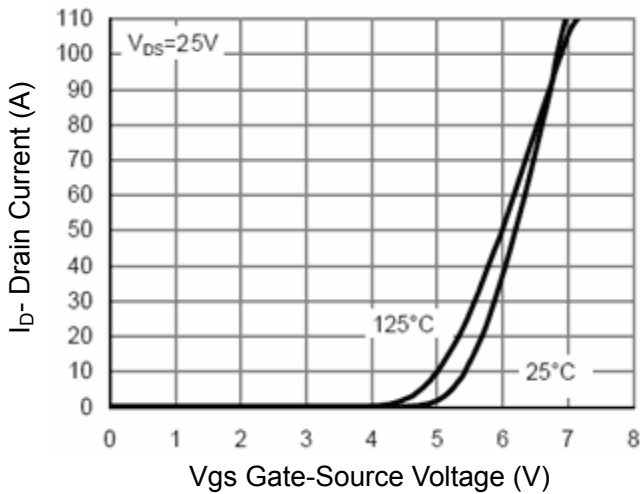


Figure 2 Transfer Characteristics

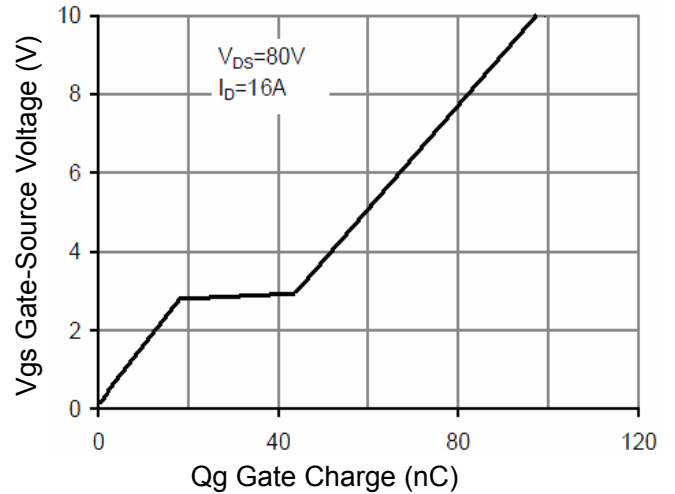


Figure 5 Gate Charge

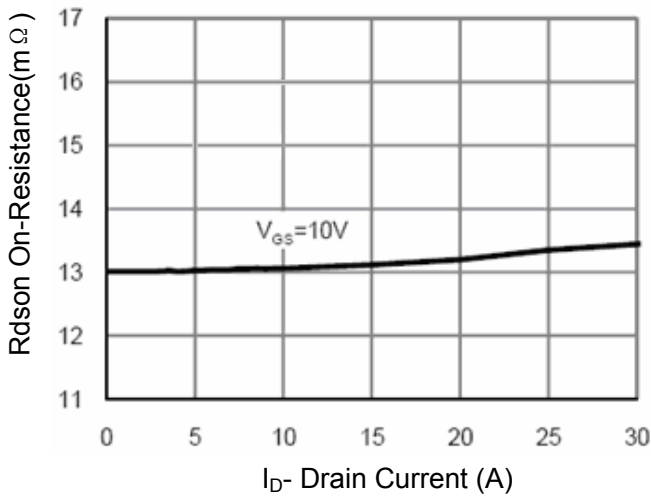


Figure 3 Rdson- Drain Current

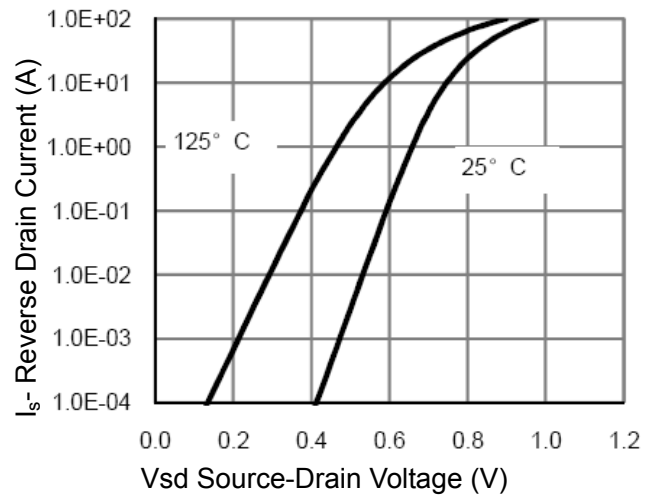


Figure 6 Source- Drain Diode Forward

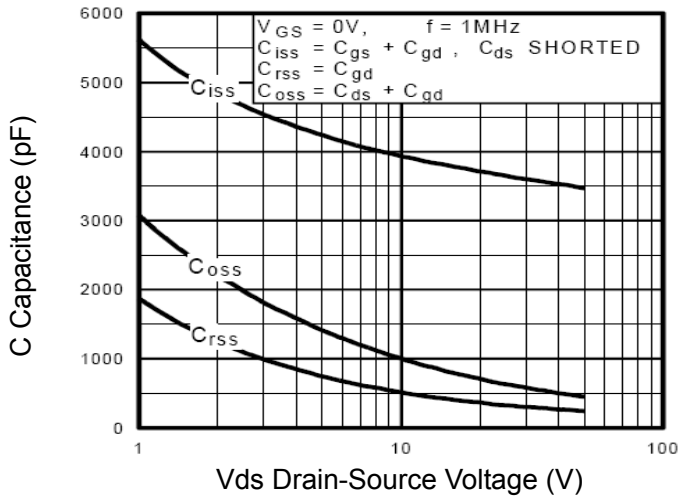


Figure 7 Capacitance vs Vds

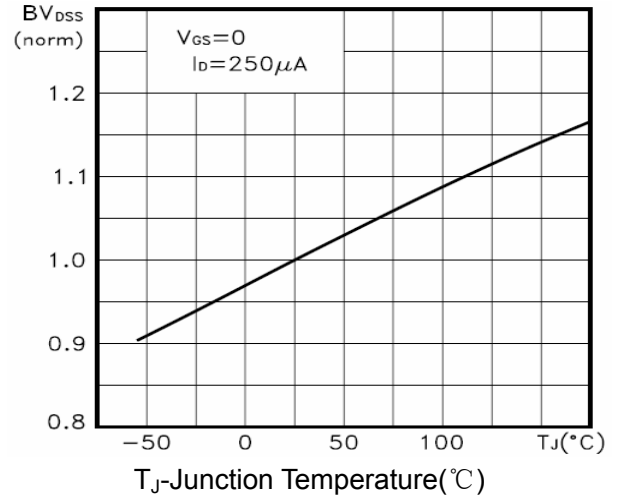


Figure 9 BV_{DSS} vs Junction Temperature

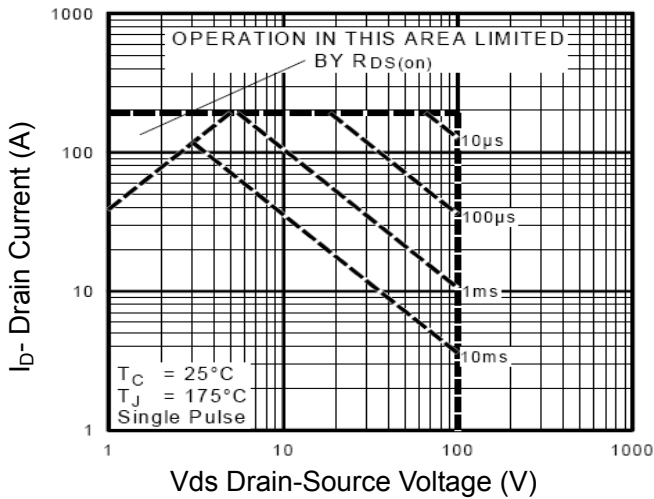


Figure 8 Safe Operation Area

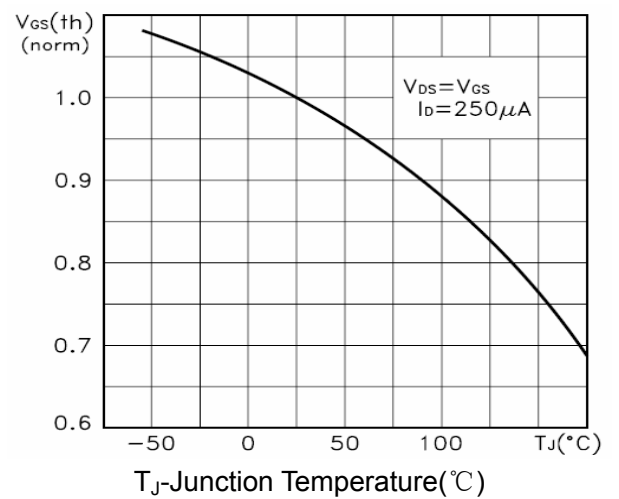


Figure 10 $V_{GS(th)}$ vs Junction Temperature

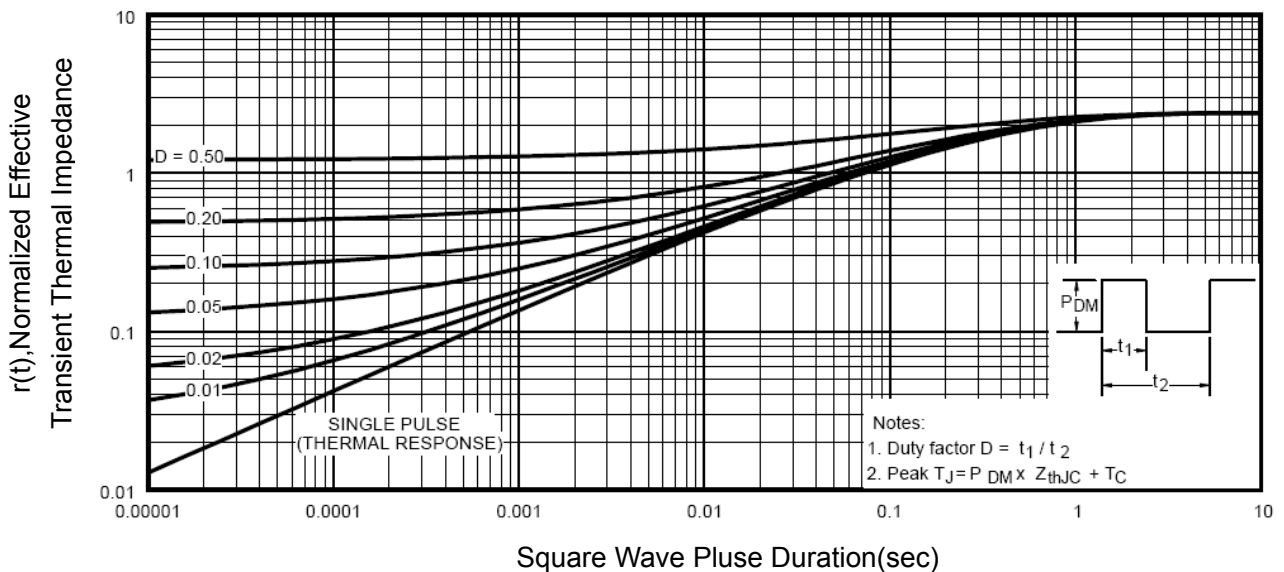
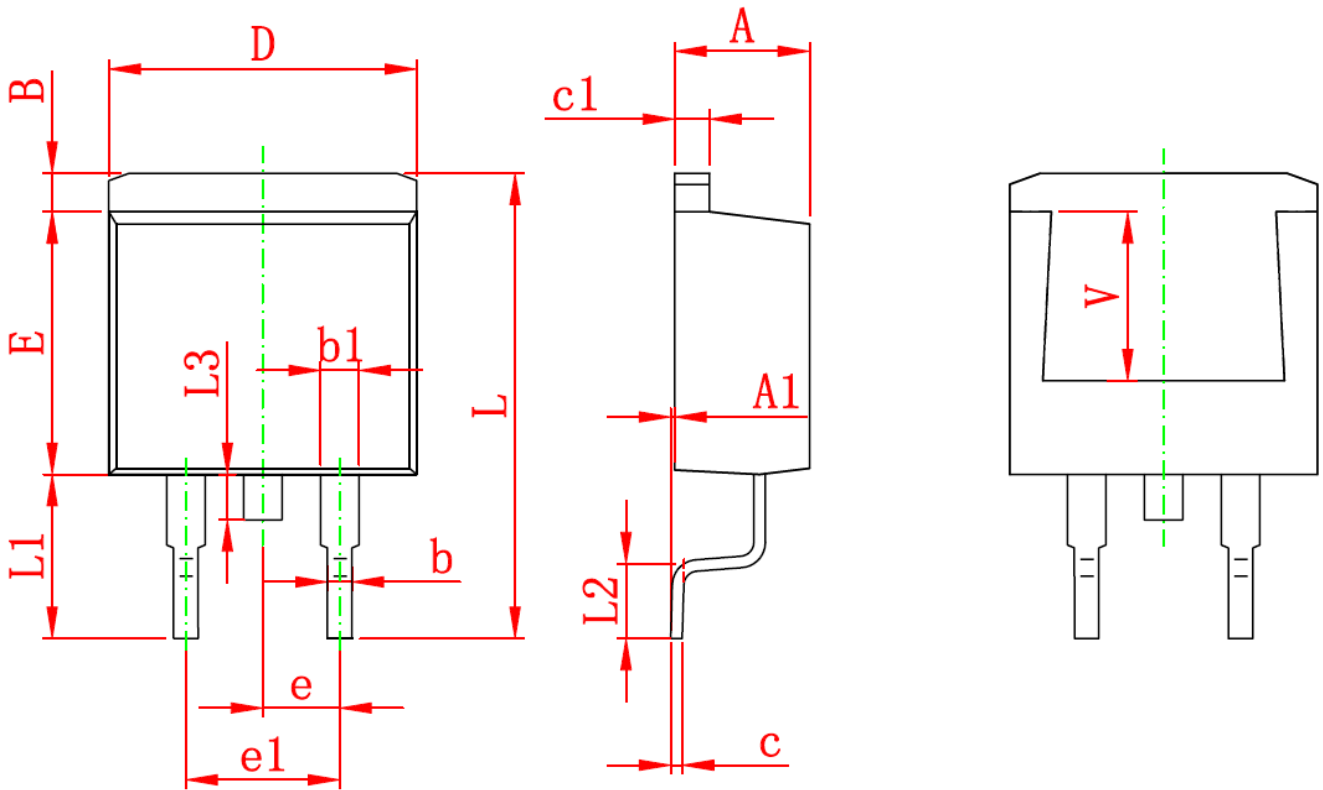


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 (TYP.)		0.100 (TYP.)	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220 REF.	

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